

Product Bulletin

Document # : PB21700X Issue Date: 14 April 2017

Title of Change:	Datasheet update for EFC2J004NUZTDG							
Effective date:	14 April 2017							
Contact information:	Contact your local ON Semiconductor Sales Office or Osamu Akaki <osamu.akaki@onsemi.com></osamu.akaki@onsemi.com>							
Type of notification: ON Semiconductor will consider this change accepted.								
Change category:	☐ Wafer Fab Change ☐ Assembly Change ☐ Test Change ☐ Other <u>Datasheet</u>							
Change Sub-Category(s): Manufacturing Site Cha Manufacturing Process								
Sites Affected: ☐ All site(s) ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐ ☐	applicable ON Semiconductor site(s): External Foundry/Subcon site							

Description and Purpose:

This PB is being issued to announce the updates done to the Datasheet of EFC2J004NUZTDG:

- RSS(on) spec with board
- Source current based on RSS(on)
- Switching time by gate resistance 10kOhm

CURRENT

ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 3)

Parameter	Symbol	Conditions		Value			Unit
raiametei				min	typ	max	Unit
Source to Source Breakdown Voltage	V(BR)SSS	I _S = 1 mA, V _{GS} = 0 V	Test Circuit 1	12			٧
Zero-Gate Voltage Source Current	ISSS	Vss = 10 V, Vgs = 0 V	Test Circuit 1			1	μА
Gate to Source Leakage Current	IGSS	$V_{GS} = \pm 8 \text{ V}, V_{SS} = 0 \text{ V}$	Test Circuit 2			±1	μА
Gate Threshold Voltage	V _{GS} (th)	V _{SS} = 6 V, I _S = 1 mA	Test Circuit 3	0.4		1.3	V
Static Source to Source On-State Resistance	R _{SS} (on)	I _S = 5 A, V _{GS} = 4.5 V	Test Circuit 4	3.1	4.5	5.9	mΩ
		I _S = 5 A, V _{GS} = 3.8 V	Test Circuit 4	3.5	5.0	6.5	mΩ
		IS = 5 A, VGS = 3.1 V	Test Circuit 4	4.0	5.8	8.2	mΩ
		I _S = 5 A, V _{GS} = 2.5 V	Test Circuit 4	5.2	7.5	11.0	mΩ
Turn-ON Delay Time	t _d (on)				180		ns
Rise Time	t _r	V _{SS} = 6 V, V _{GS} = 4.5 V, I _S = 3 A Test Circuit 5			300		ns
Turn-OFF Delay Time	t _d (off)				1,700		ns
Fall Time	tf			660		ns	
Total Gate Charge	Qg	V _{SS} = 6 V, V _{GS} = 4.5 V,	Is = 15 A Test Circuit 6		36		nC
Forward Source to Source Voltage	VF(S-S)	I _S =3A, V _{GS} =0V	Test Circuit 7		0.76		٧

Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TEM001094 Rev. H Page 1 of 2



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UPDATED

ELECTRICAL CHARACTERISTICS at Ta = 25°C (Notes 3, 4)

Parameter	Symbol	Conditions		Value			1.1
Parameter				min	typ	max	Unit
Source to Source Breakdown Voltage	V(BR)SSS	I _S = 1 mA, V _{GS} = 0 V	Test Circuit 1	12			٧
Zero-Gate Voltage Source Current	ISSS	V _{SS} = 10 V, V _{GS} = 0 V	Test Circuit 1			1	μА
Gate to Source Leakage Current	IGSS	$V_{GS} = \pm 8 \text{ V}, V_{SS} = 0 \text{ V}$	Test Circuit 2			±1	μА
Gate Threshold Voltage	V _{GS} (th)	V _{SS} = 6 V, I _S = 1 mA	Test Circuit 3	0.4		1.3	٧
Static Source to Source On-State Resistance (Note 4)	R _{SS} (on)	I _S = 5 A, V _{GS} = 4.5 V	Test Circuit 4	3.7	5.4	7.1	mΩ
		I _S = 5 A, V _{GS} = 3.8 V	Test Circuit 4	4.1	5.9	7.7	mΩ
		I _S = 5 A, V _{GS} = 3.1 V	Test Circuit 4	4.6	6.7	9.5	mΩ
		I _S = 5 A, V _{GS} = 2.5 V	Test Circuit 4	5.8	8.4	12.4	mΩ
Turn-ON Delay Time	t _d (on)		/, I _S = 5 A Test Circuit 5		15		μS
Rise Time	tr	V _{SS} = 5 V, V _{GS} = 3.8 V,			35		μS
Turn-OFF Delay Time	t _d (off)	Rg = 10 kΩ			100		μS
Fall Time	tf	Ī			75		μS
Total Gate Charge Qg		V _{SS} = 6 V, V _{GS} = 4.5 V,	I _S = 14 A Test Circuit 6		36		nC
Forward Source to Source Voltage	VF(S-S)	Is = 3 A, VGS = 0 V	Test Circuit 7		0.76		٧

Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

The change will not impact form, fit, or function of product.

List of affected Standard Parts:

EFC2J004NUZTDG

TEM001094 Rev. H Page 2 of 2

Note 4: Mounted on ON Semiconductor board.